

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3644	(MOS) same (resistive)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 12:46
L2	6	1 and (resistor or resistive) near ((silicon adj nitride) or (silicon adj oxynitride) or (SiN) or (SiON))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 12:54
L3	2	"6483152".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 13:04
L4	1	"4367580".PN.	USPAT; USOCR	OR	OFF	2005/08/22 12:55
L5	1	"5126279".PN.	USPAT; USOCR	OR	OFF	2005/08/22 12:58
L6	1	"5618749".PN.	USPAT; USOCR	OR	OFF	2005/08/22 12:59
L7	33	"5618749"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 13:04
L8	1	"4968645".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:09
L9	1	"5135882".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:09
L10	1	"5168076".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:09
L11	1	"5356826".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:10
L12	1	"5462894".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:10
L13	1	"5500553".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:10
L14	1	"5618749".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:13
L15	1	"5656524".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:14

L16	1	"5705436".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:24
L17	1	"5780333".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:24
L18	1	"5767544".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:25
L19	1	"5736421".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:25
L20	1	"5618749".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:27
L21	1	"4367580".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:28
L22	1	"3988824".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:29
L23	1	"4367580".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:29
L24	1	"4971924".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:29
L25	1	"5013678".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:30
L26	1	"5120572".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:30
L27	1	"5173437".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:31
L28	1	"5187122".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:31
L29	1	"5393691".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:32
L30	1	"5397729".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:33
L31	1	"5470775".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:33
L32	1	"5500387".PN.	USPAT; USOCR	OR	OFF	2005/08/22 13:33
S1	1009	257/379	US-PGPUB; USPAT	OR	OFF	2005/01/25 11:19
S2	295	S1 and mos and resistor	US-PGPUB; USPAT	OR	OFF	2005/01/25 11:20
S3	280	S2 and gate	US-PGPUB; USPAT	OR	OFF	2005/01/25 11:20
S4	61	S3 and poly	US-PGPUB; USPAT	OR	OFF	2005/01/25 11:20
S5	1	S2 and ((high and low) adj (breakdown adj voltage adj transistor)) and resistor	US-PGPUB; USPAT	OR	OFF	2005/01/25 15:16

S6	1	S2 and ((high and low) adj (breakdown adj voltage adj transistor)) and resist\$	US-PGPUB; USPAT	OR	OFF	2005/01/25 15:16
S7	1	257/380 and ((high and low) adj (breakdown adj voltage adj transistor)) and resist\$	US-PGPUB; USPAT	OR	OFF	2005/01/25 15:16
S8	4	S2 and ((high and low) adj (breakdown adj voltage)) and resist\$	US-PGPUB; USPAT	OR	OFF	2005/01/25 15:22
S9	29	((high and low) adj (breakdown adj voltage adj transistor)) and resist\$	US-PGPUB; USPAT	OR	OFF	2005/01/25 15:23